

16.12.1985

Japanese Unexamined Patent Application Publication No. 60-
254432

In carrying out the present invention, inorganic resist materials such as chalcogenide alloys can be advantageously used as a photosensitive film. Useful examples of such inorganic materials include alloys such as TeGeSn, TeGe, TeSe, AsS, AsSe, SbS, and SbSe. For the formation of a film composed of such a material, a sputtering method, an electron-beam heating method, or the like can be employed besides a vacuum evaporation method. For example, when an optical disc is fabricated, an inorganic resist can be formed on a glass disc having a predetermined dimension by an evaporation method.